

LPCVD	Tube 3	Material	Poly Silicon Crystalline	
Uniformity:	Film Uniformity Variance < 2% across 4" wafer			
Gases	Flow Rate	Time (minutes)	Film Thickness (nm)	Deposition rate (nm/min)
Temperature	620 C	10	86.8	8.68
Comments: With Wet Etch step height for 50 min sample is 478.7 nm and Dep. Rate is 9.57 nm/min		20	148.3	7.42
		30	270.4	9.01
		40	378.4	9.46
		50	504.4	10.09
		60	584.3	9.74

